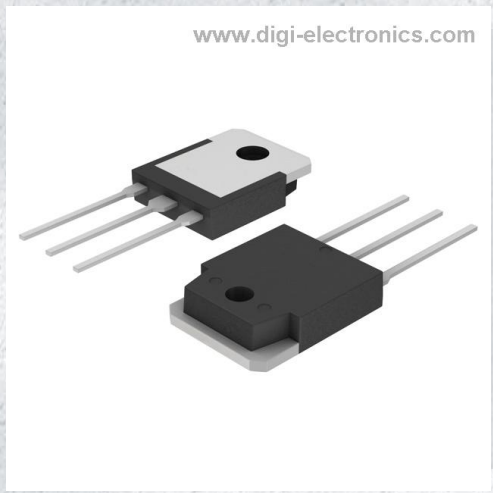
FQA11N90 Datasheet



DiGi Electronics Part Number	FQA11N90-DG
Manufacturer	onsemi
Manufacturer Product Number	FQA11N90
Description	MOSFET N-CH 900V 11.4A TO3P
Detailed Description	N-Channel 900 V 11.4A (Tc) 300W (Tc) Through Hole TO-3P

https://www.DiGi-Electronics.com

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
FQA11N90	onsemi
Series:	Product Status:
QFET®	Obsolete
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
900 V	11.4A (Tc)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
10V	960mOhm @ 5.7A, 10V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
5V @ 250µA	94 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±30V	3500 pF @ 25 V
FET Feature:	Power Dissipation (Max):
-	300W (Tc)
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Through Hole
Supplier Device Package:	Package / Case:
TO-3P	TO-3P-3, SC-65-3
Base Product Number:	
FQA1	

Environmental & Export classification

Moisture Sensitivity Level (MSL):	REACH Status:
1 (Unlimited)	REACH Unaffected
ECCN:	HTSUS:
EAR99	8541.29.0095

FAIRCHILD SEMICONDUCTOR®

April 2013

FQA11N90 / FQA11N90_F109

N-Channel QFET® MOSFET

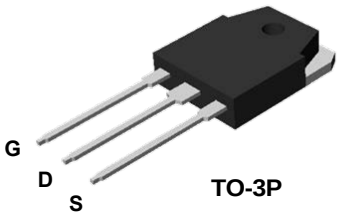
900 V, 11.4 A, 960 mΩ

Features

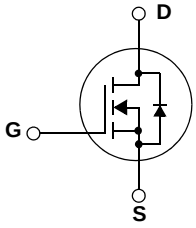
- 11.4 A, 900 V, $R_{DS(on)}$ = 960 mΩ (Max.) @ V_{GS} = 10 V, ID = 5.7 A
- Low Gate Charge (Typ. 72 nC)
- Low Crss (Typ. 30 pF)
- 100% Avalanche Tested
- RoHS Compliant

Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor®'s proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.



TO-3P



Absolute Maximum Ratings

Symbol	Parameter		FQA11N90	Unit
V_{DSS}	Drain-Source Voltage		900	V
I_D	Drain Current - Continuous (T_C = 25°C)		11.4	A
	- Continuous (T_C = 100°C)		7.2	A
I_{DM}	Drain Current - Pulsed	(Note 1)	45.6	A
V_{GSS}	Gate-Source Voltage		± 30	V
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	1000	mJ
I_{AR}	Avalanche Current	(Note 1)	11.4	A
E_{AR}	Repetitive Avalanche Energy	(Note 1)	30	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.0	V/ns
P_D	Power Dissipation (T_C = 25°C)		300	W
	- Derate above 25°C		2.38	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	°C
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C

Thermal Characteristics

Symbol	Parameter	FQA11N90	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.42	°C/W
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink, Typ.	0.24	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	°C/W

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FQA11N90	FQA11N90	TO-3P	--	--	30
FQA11N90	FQA11N90_F109	TO-3PN	--	--	30

Electrical Characteristics

T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 μA	900	--	--	V
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C	--	1.0	--	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 900 V, V_{GS} = 0 V	--	--	10	μA
		V_{DS} = 720 V, T_C = 125°C	--	--	100	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	V_{GS} = 30 V, V_{DS} = 0 V	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = -30 V, V_{DS} = 0 V	--	--	-100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 μA	3.0	--	5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	V_{GS} = 10 V, I_D = 5.7 A	--	0.75	0.96	Ω
g_{FS}	Forward Transconductance	V_{DS} = 50 V, I_D = 5.7 A (Note 4)	--	12	--	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25 V, V_{GS} = 0 V, f = 1.0 MHz	--	2700	3500	pF
C_{oss}	Output Capacitance		--	260	340	pF
C_{rss}	Reverse Transfer Capacitance		--	30	40	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 450 V, I_D = 11.4A, R_G = 25 Ω (Note 4, 5)	--	65	140	ns
t_r	Turn-On Rise Time		--	135	280	ns
$t_{d(off)}$	Turn-Off Delay Time		--	165	340	ns
t_f	Turn-Off Fall Time		--	90	190	ns
Q_g	Total Gate Charge	V_{DS} = 720 V, I_D = 11.4A, V_{GS} = 10 V (Note 4, 5)	--	72	94	nC
Q_{gs}	Gate-Source Charge		--	16	--	nC
Q_{gd}	Gate-Drain Charge		--	35	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		--	--	11.4	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	45.6	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0 V, I_S =11.4 A	--	--	1.4	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0 V, I_S = 11.4 A, dI_F / dt = 100 A/μs (Note 4)	--	850	--	ns
Q_{rr}	Reverse Recovery Charge		--	11.2	--	μC

NOTES:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. L = 15mH, I_{AS} =11.4A, V_{DD} = 50V, R_G = 25 Ω, Starting T_J = 25°C
3. I_{SD} ≤ 11.4A, di/dt ≤200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
4. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%
5. Essentially independent of operating temperature

Typical Performance Characteristics

Figure 1. On-Region Characteristics

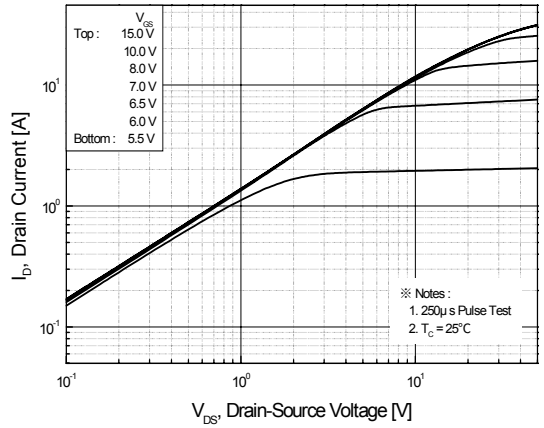


Figure 2. Transfer Characteristics

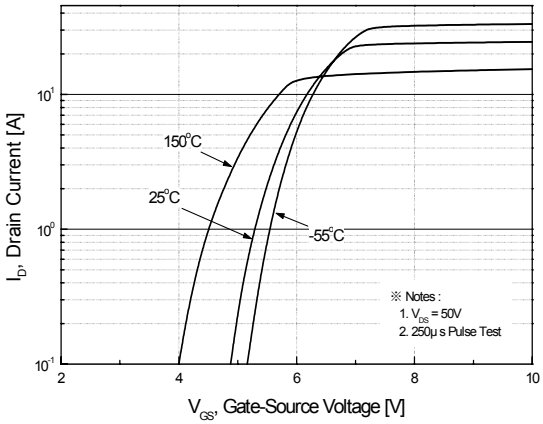


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

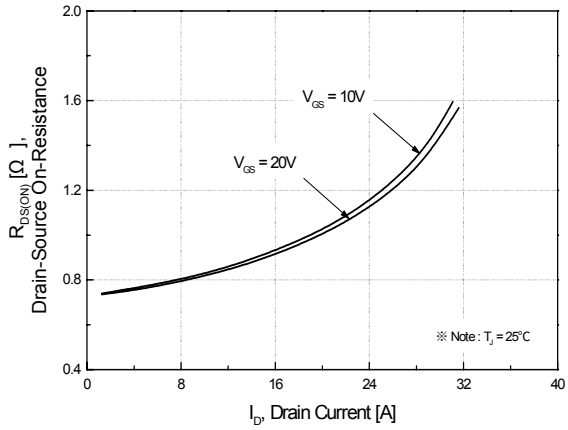


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue

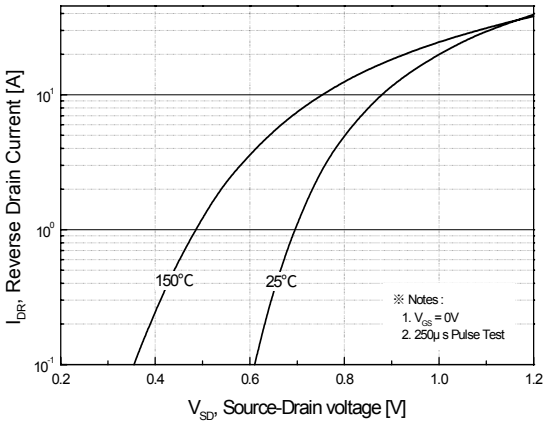


Figure 5. Capacitance Characteristics

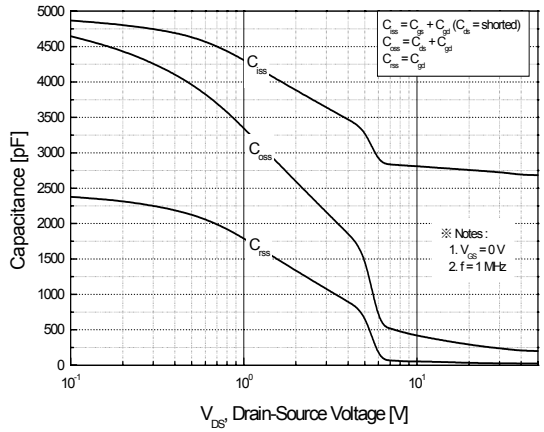
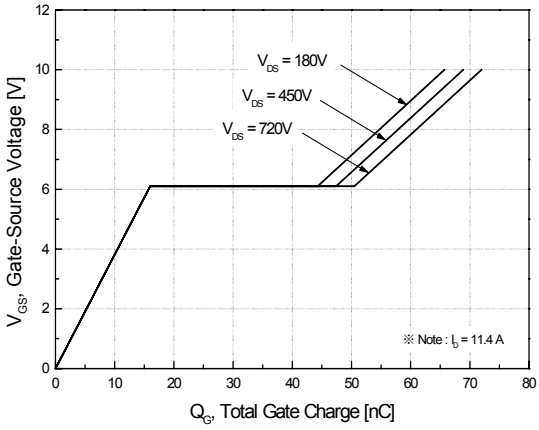


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

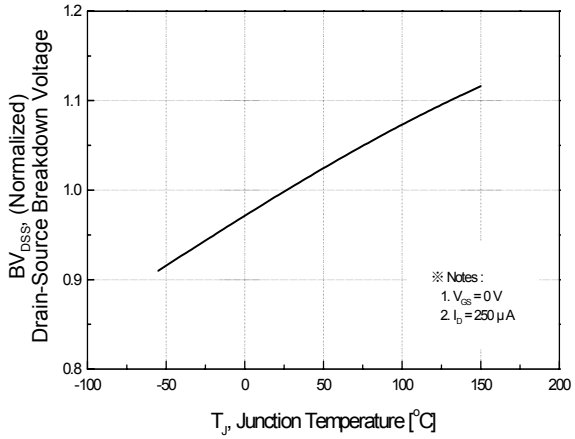


Figure 8. On-Resistance Variation vs. Temperature

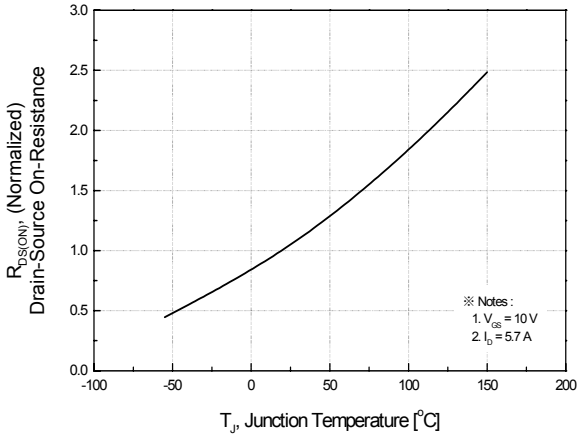


Figure 9. Maximum Safe Operating Area

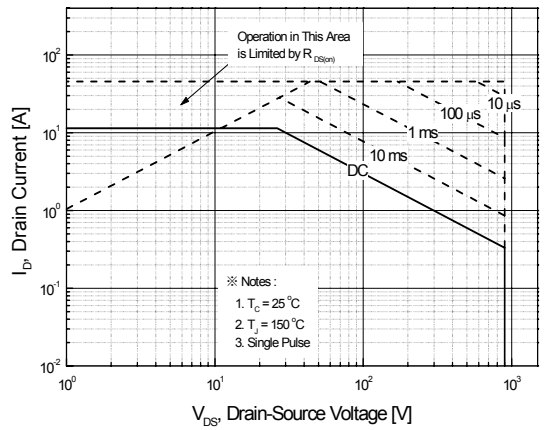


Figure 10. Maximum Drain Current vs. Case Temperature

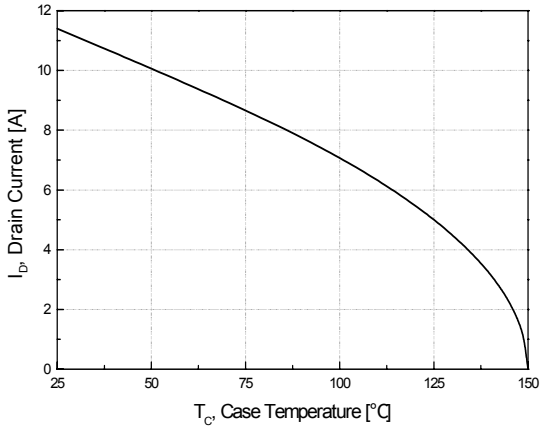
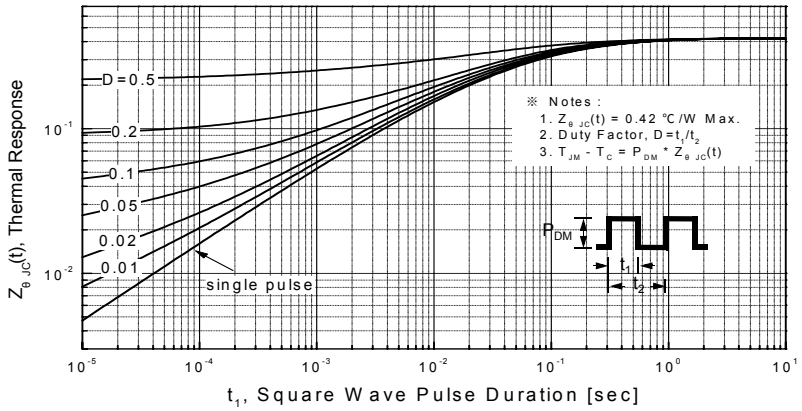
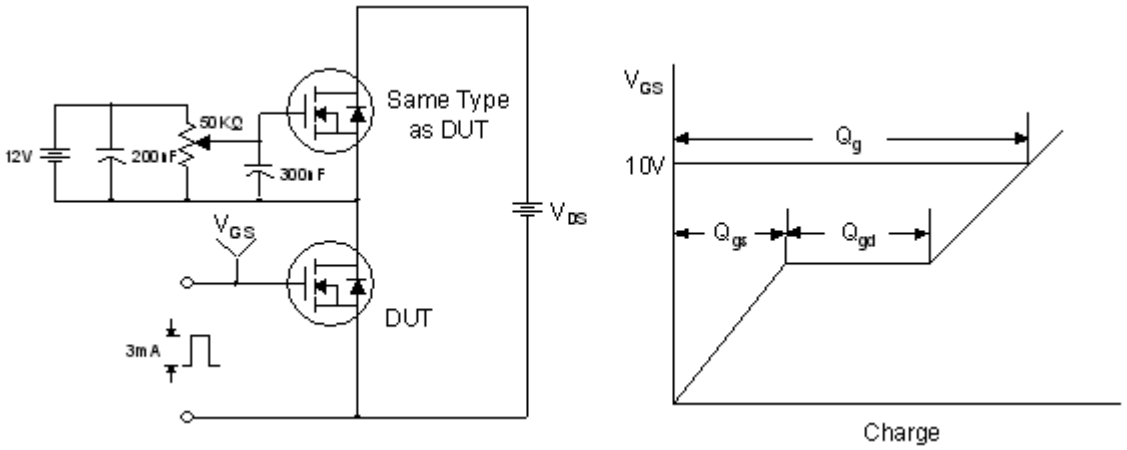


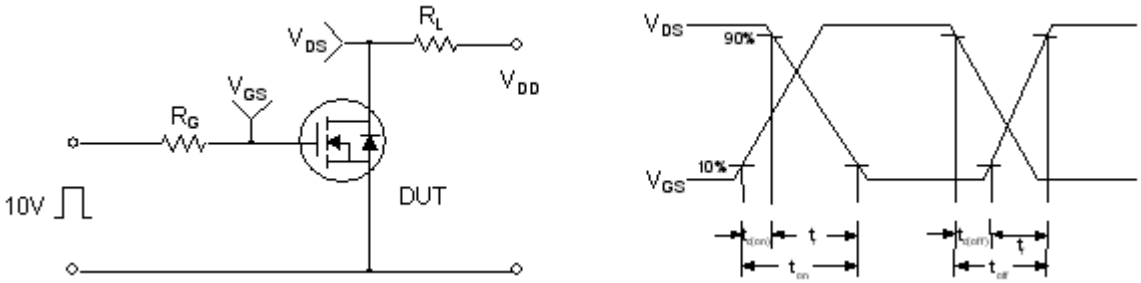
Figure 11. Transient Thermal Response Curve



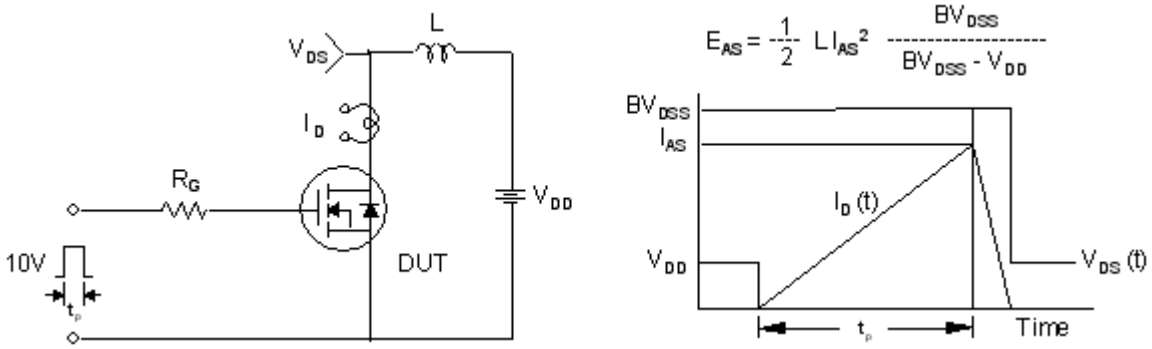
Gate Charge Test Circuit & Waveform



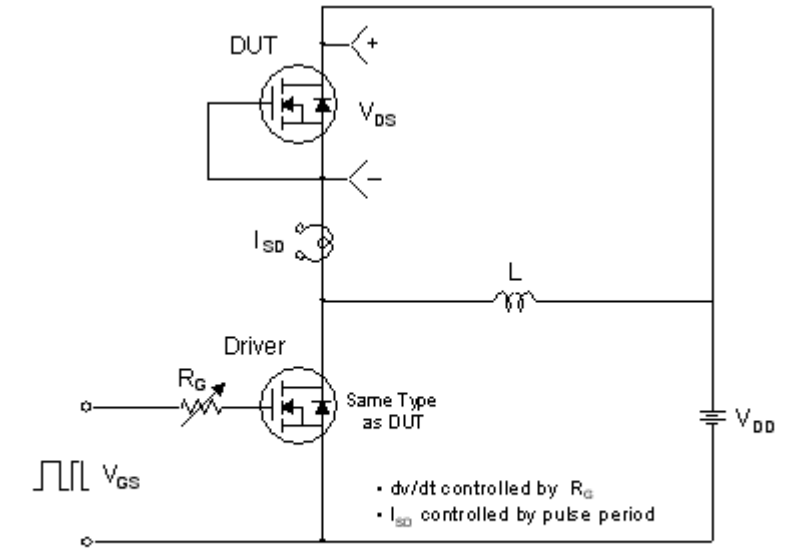
Resistive Switching Test Circuit & Waveforms

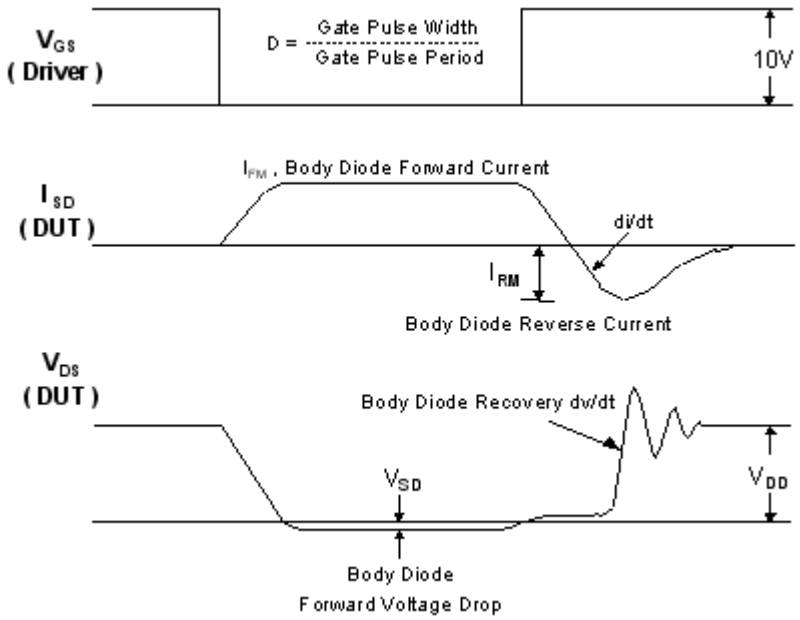


Unclamped Inductive Switching Test Circuit & Waveforms



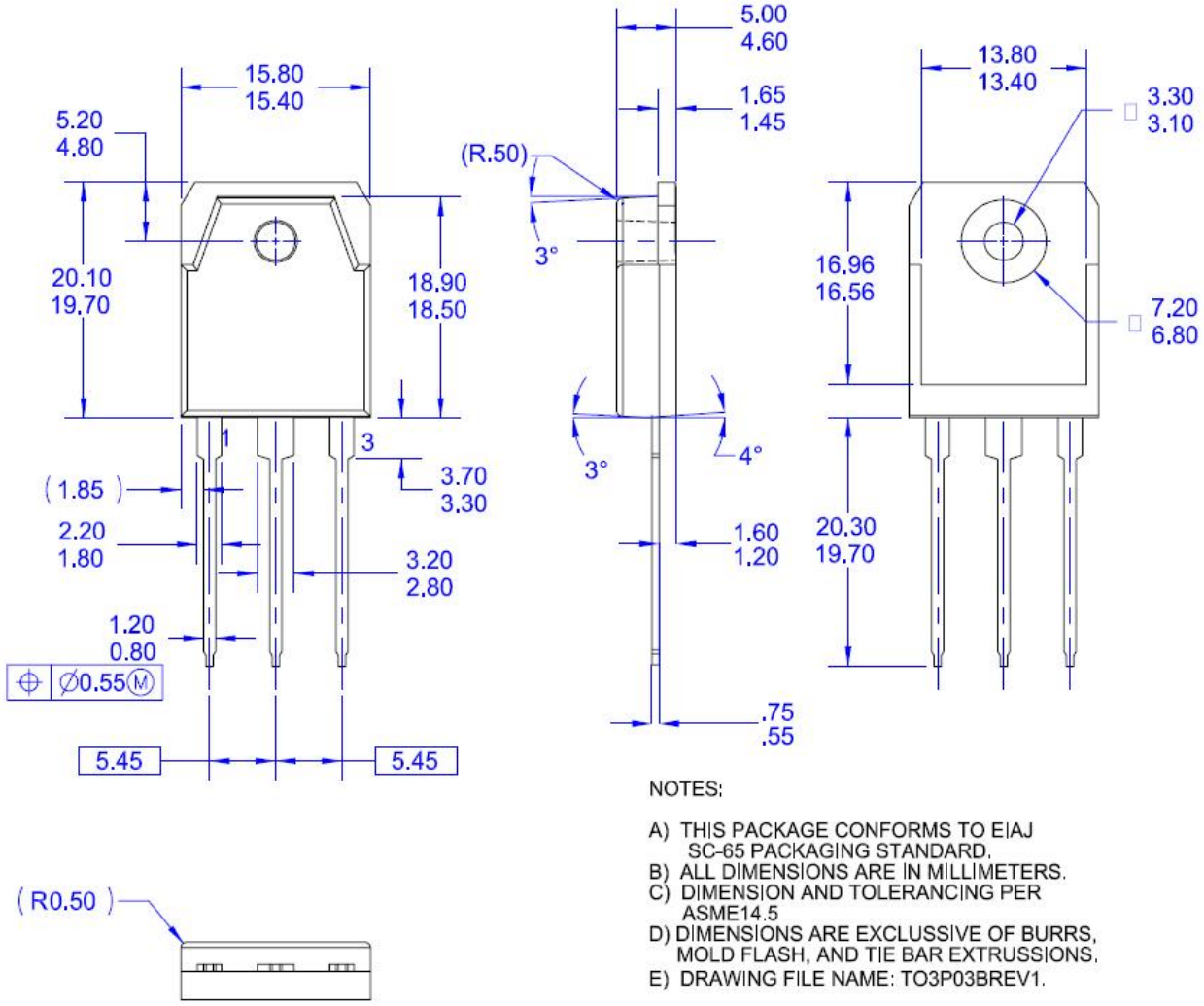
Peak Diode Recovery dv/dt Test Circuit & Waveforms





Mechanical Dimensions

TO-3P



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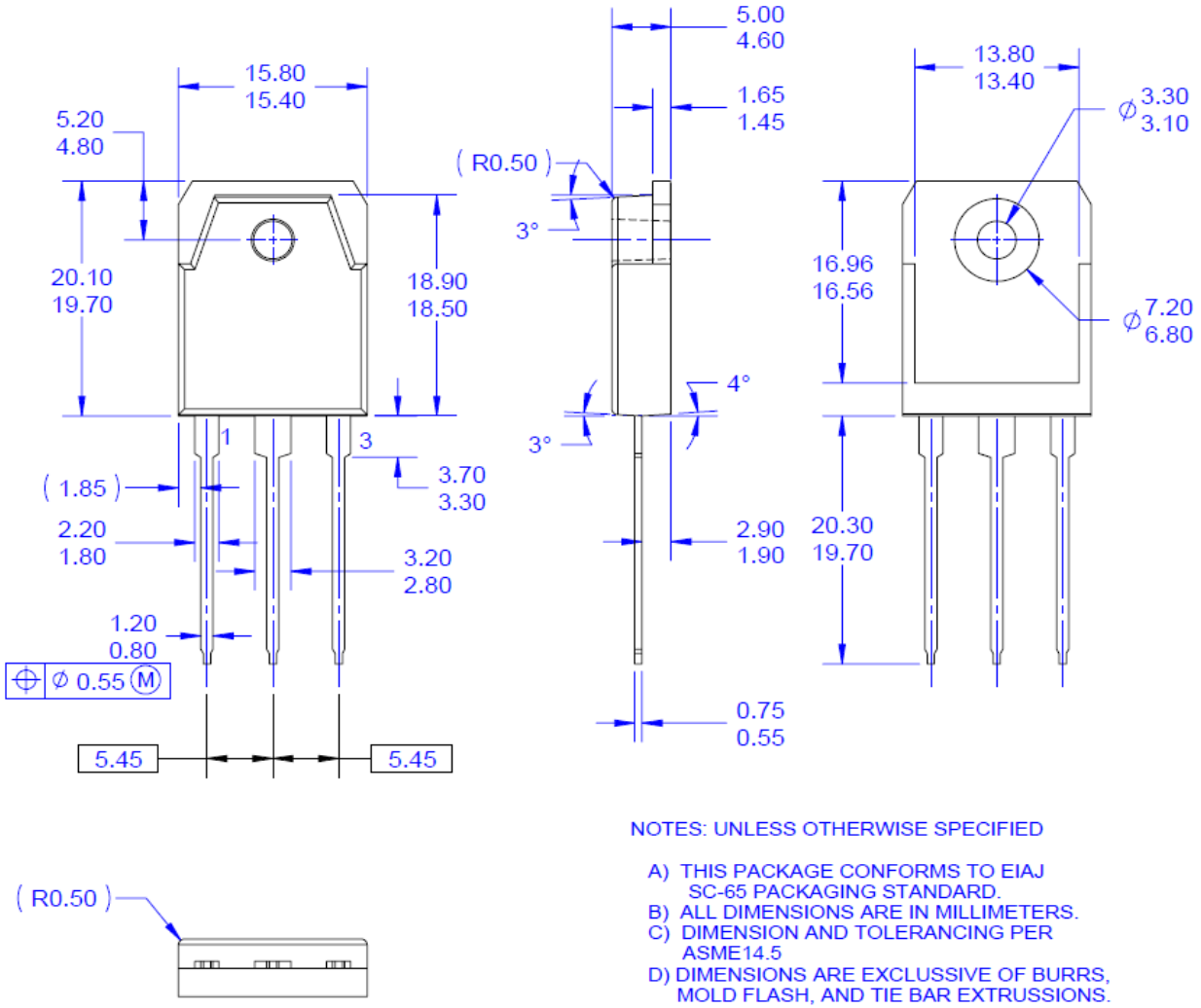
Dimensions in Millimeters

Mechanical Dimensions

TO-3PN



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Dimensions in Millimeters

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No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

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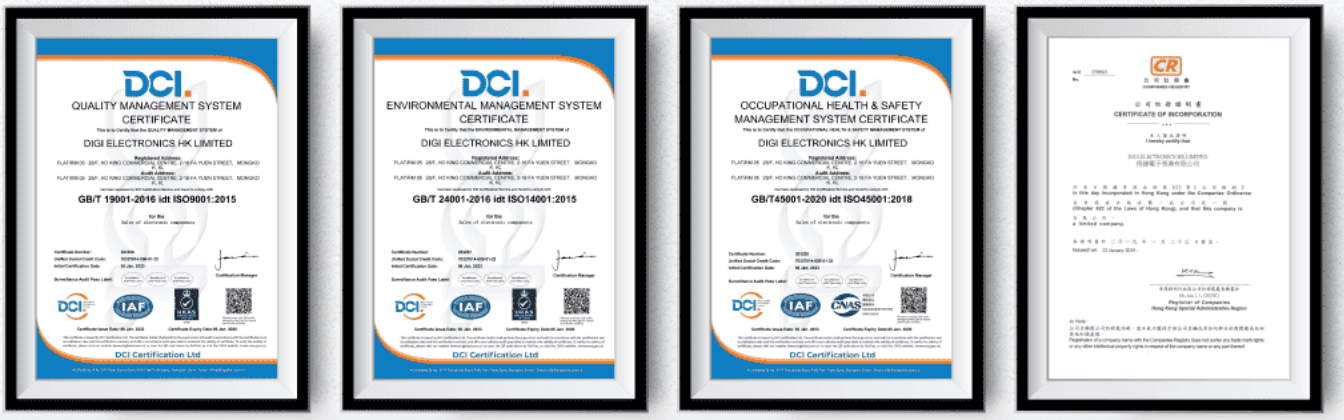

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